NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI CBSL15** is Designed for

FEATURES:

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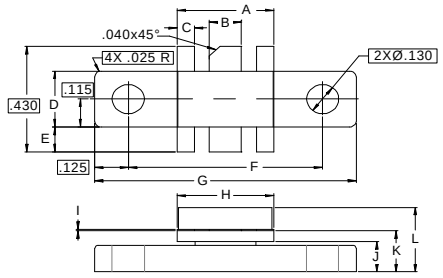
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	2.5 A
V_{CBO}	48 V
V_{CEO}	30 V
V_{EBO}	4.0 V
P_{DISS}	29 W @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +150 ^{O}C
θ_{JC}	6.0 ^{O}C/W

PACKAGE STYLE .230 6L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.355 / 9.02	.365 / 9.27
B	.115 / 2.92	.125 / 3.18
C	.075 / 1.91	.085 / 2.16
D	.225 / 5.72	.235 / 5.97
E	.090 / 2.29	.110 / 2.79
F	.720 / 18.29	.730 / 18.54
G	.970 / 24.64	.980 / 24.89
H	.355 / 9.02	.365 / 9.27
I	.004 / 0.10	.006 / 0.15
J	.120 / 3.05	.130 / 3.30
K	.160 / 4.06	.180 / 4.57
L	.230 / 5.84	.260 / 6.60

ORDER CODE: ASI10581

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 50 mA	48			V
BV_{CEO}	I_C = 20 mA	25			V
BV_{EBO}	I_E = 5 mA	3.5	4.0	---	V
I_{CBO}	V_{CB} = 24 V			1.0	mA
h_{FE}	V_{CE} = 10 V I_C = 100 mA	20		100	---
C_{OB}	V_{CB} = 24 V f = 1.0 MHz			25	pF
P_G	V_{CC} = 24 V I_{CQ} = 75 mA f = 960 MHz	8.0			dB
η_C	P_{OUT} = 15 W		50		%